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**REVISION HISTORY**

Revision 0: Initial Version

## AD5290—SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS—10 kΩ VERSION

$V_{DD}/V_{SS} = \pm 15\text{ V} \pm 10\%$ ,  $V_A = +V_{DD}$ ,  $V_B = V_{SS}/0\text{ V}$ ,  $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ , unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ <sup>1</sup>	Max	Unit
DC CHARACTERISTICS RHEOSTAT MODE						
Resistor Differential NL <sup>2</sup>	R-DNL	$R_{WB}$ , $V_A = \text{NC}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$	-1	±0.5	+1	LSB
Resistor Nonlinearity <sup>2</sup>	R-INL	$R_{WB}$ , $V_A = \text{NC}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$	-1	±0.5	+1	LSB
Nominal Resistor Tolerance	$\Delta R_{AB}$	$T_A = +25^\circ\text{C}$	-30		+30	%
Resistance Temperature Coefficient <sup>3</sup>	$(\Delta R_{AB}/R_{AB})/\Delta T \cdot 10^6$	$V_{AB} = V_{DD}$ , wiper = no connect		35		ppm/°C
Wiper Resistance	$R_W$	$V_{DD}/V_{SS} = \pm 15\text{ V}$ $V_{DD}/V_{SS} = \pm 5\text{ V}$		120 260	200	$\Omega$ $\Omega$
DC CHARACTERISTICS POTENTIOMETER DIVIDER MODE						
Integral Nonlinearity <sup>4</sup>	INL	$V_{DD}/V_{SS} = \pm 15\text{ V}$	-1	±0.5	+1	LSB
Differential Nonlinearity <sup>4</sup>	DNL	$V_{DD}/V_{SS} = \pm 15\text{ V}$	-1	±0.5	+1	LSB
Voltage Divider Temperature Coefficient	$(\Delta V_W/V_W)/\Delta T \cdot 10^6$	Code = 0x80		5		ppm/°C
Full-Scale Error	$V_{WFSE}$	Code = 0xFF, $V_{DD}/V_{SS} = \pm 15\text{ V}$	-3	-1.5	0	LSB
Zero-Scale Error	$V_{WZSE}$	Code = 0x00, $V_{DD}/V_{SS} = \pm 15\text{ V}$	0	+1.5	+3	LSB
RESISTOR TERMINALS						
Voltage Range <sup>5</sup>	$V_{A,B,W}$		$V_{SS}$		$V_{DD}$	V
Capacitance <sup>6</sup> A, B	$C_{A,B}$	$f = 1\text{ MHz}$ , measured to GND, code = 0x80		45		pF
Capacitance <sup>6</sup>	$C_W$	$f = 1\text{ MHz}$ , measured to GND, code = 0x80		60		pF
Common-Mode Leakage	$I_{CM}$	$V_A = V_B = V_W$		1		nA
DIGITAL INPUTS AND OUTPUTS						
Input Logic High ( $\overline{CS}$ , CLK, SDI)	$V_{IH}$	$V_{DD} = 5\text{ V}$ or $15\text{ V}$	2.4			V
Input Logic Low ( $\overline{CS}$ , CLK, SDI)	$V_{IL}$	$V_{DD} = 5\text{ V}$ or $15\text{ V}$			0.8	V
Output Logic High (SDO)	$V_{OH}$	$R_{PULL-UP} = 2.2\text{ k}\Omega$ to $5\text{ V}$	4.9			V
Output Logic Low (SDO)	$V_{OL}$	$I_{OL} = 1.6\text{ mA}$ , $V_{LOGIC} = 5\text{ V}$ , $V_{DD} = 15\text{ V}$			0.4	V
Input Current	$I_{IL}$	$V_{IN} = 0\text{ V}$ or $5\text{ V}$			±1	μA
Input Capacitance <sup>6</sup>	$C_{IL}$			5		pF
POWER SUPPLIES						
Power Supply Range	$V_{DD}/V_{SS}$	Dual-supply range	±4.5		±16.5	V
Power Supply Range	$V_{DD}$	Single-supply range, $V_{SS} = 0$	4.5		33	V
Positive Supply Current	$I_{DD}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			2	mA
		$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 5\text{ V}$		12	25	μA
Negative Supply Current	$I_{SS}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			-0.1	mA
		$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 5\text{ V}$			-0.1	mA
Power Dissipation <sup>7</sup>	$P_{DISS}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			31.5	mW
Power Supply Rejection Ratio	PSRR	$\Delta V_{DD}/\Delta V_{SS} = \pm 15\text{ V} \pm 10\%$	-0.2	±0.05	+0.2	%/%
DYNAMIC CHARACTERISTICS <sup>6,8,9</sup>						
Bandwidth -3 dB	BW	Code = 0x80		470		kHz
Total Harmonic Distortion	THD <sub>W</sub>	$V_A = 1\text{ V rms}$ , $V_B = 0\text{ V}$ , $f = 1\text{ kHz}$		0.006		%
$V_W$ Settling Time	$t_s$	$V_A = 10\text{ V}$ , $V_B = 0\text{ V}$ , ±1 LSB error band		4		μs
Resistor Noise Voltage	$e_{N\_WB}$	$R_{WB} = 5\text{ k}\Omega$ , $f = 1\text{ kHz}$		0.9		nV $\sqrt{\text{Hz}}$

<sup>1</sup> Typical represent average reading at  $+25^\circ\text{C}$ ,  $V_{DD} = +15\text{ V}$ , and  $V_{SS} = -15\text{ V}$ .

<sup>2</sup> Resistor position nonlinearity error R-INL is the deviation from an ideal value measured between the maximum resistance and the minimum resistance wiper positions. R-DNL measures the relative step change from an ideal value measured between successive tap positions. Parts are guaranteed monotonic.

<sup>3</sup> All parts have a 35 ppm/°C temperature coefficient.

- 
- <sup>4</sup> INL and DNL are measured at  $V_w$  with the RDAC configured as a potentiometer divider similar to a voltage output digital-to-analog converter.  $V_A = V_{DD}$  and  $V_B = 0$  V. DNL specification limits of  $\pm 1$  LSB maximum are guaranteed monotonic operating conditions.
- <sup>5</sup> Resistor Terminals A, B, and W have no limitations on polarity with respect to each other.
- <sup>6</sup> Guaranteed by design and not subject to production test.
- <sup>7</sup>  $P_{DISS}$  is calculated from  $(I_{DD} \times V_{DD}) + \text{abs}(I_{SS} \times V_{SS})$ . CMOS logic level inputs result in minimum power dissipation.
- <sup>8</sup> Bandwidth, noise, and settling times are dependent on the terminal resistance value chosen. The lowest R value results in the fastest settling time and highest bandwidth. The highest R value results in the minimum overall power consumption.
- <sup>9</sup> All dynamic characteristics use  $V_{DD} = +15$  V and  $V_{SS} = -15$  V.

**ELECTRICAL CHARACTERISTICS—50 kΩ, 100 kΩ VERSIONS**

$V_{DD}/V_{SS} = \pm 15\text{ V} \pm 10\%$  or  $\pm 5\text{ V} \pm 10\%$ ,  $V_A = +V_{DD}$ ,  $V_B = V_{SS}/0\text{ V}$ ,  $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ , unless otherwise noted.

**Table 2.**

Parameter	Symbol	Conditions	Min	Typ <sup>1</sup>	Max	Unit
<b>DC CHARACTERISTICS RHEOSTAT MODE</b>						
Resistor Differential NL <sup>2</sup>	R-DNL	$R_{WB}$ , $V_A = \text{NC}$ ,	-1	±0.5	+1	LSB
Resistor Nonlinearity <sup>2</sup>	R-INL	$R_{WB}$ , $V_A = \text{NC}$ , $R_{AB} = 50\text{ k}\Omega$	-1.5	±0.5	+1.5	LSB
		$R_{WB}$ , $V_A = \text{NC}$ , $R_{AB} = 100\text{ k}\Omega$	-1	±0.5	+1	LSB
Nominal Resistor Tolerance	$\Delta R_{AB}$	$T_A = +25^\circ\text{C}$	-30		+30	%
Resistance Temperature Coefficient <sup>3</sup>	$(\Delta R_{AB}/R_{AB})/\Delta T \times 10^6$	$V_{AB} = V_{DD}$ , wiper = no connect		35		ppm/°C
Wiper Resistance	$R_W$	$V_{DD}/V_{SS} = \pm 15\text{ V}$		120	200	Ω
		$V_{DD}/V_{SS} = \pm 5\text{ V}$		260		Ω
<b>DC CHARACTERISTICS POTENTIOMETER DIVIDER MODE</b>						
Integral Nonlinearity <sup>4</sup>	INL		-1	±0.5	+1	LSB
Differential Nonlinearity <sup>4</sup>	DNL		-1	±0.5	+1	LSB
Voltage Divider Temperature Coefficient	$(\Delta V_W/V_W)/\Delta T \times 10^6$	Code = 0x80		5		ppm/°C
Full-Scale Error	$V_{WFSE}$	Code = 0xFF	-2	-0.5	0	LSB
Zero-Scale Error	$V_{WZSE}$	Code = 0x00	0	+0.5	+1	LSB
<b>RESISTOR TERMINALS</b>						
Voltage Range <sup>5</sup>	$V_{A,B,W}$		$V_{SS}$		$V_{DD}$	V
Capacitance <sup>6</sup> A, B	$C_{A,B}$	f = 1 MHz, measured to GND, code = 0x80		45		pF
Capacitance <sup>6</sup>	$C_W$	f = 1 MHz, measured to GND, code = 0x80		60		pF
Common-Mode Leakage	$I_{CM}$	$V_A = V_B = V_W$		1		nA
<b>DIGITAL INPUTS AND OUTPUTS</b>						
Input Logic High ( $\overline{CS}$ , CLK, SDI)	$V_{IH}$	$V_{DD} = 5\text{ V}$ or $15\text{ V}$	2.4			V
Input Logic Low ( $\overline{CS}$ , CLK, SDI)	$V_{IL}$	$V_{DD} = 5\text{ V}$ or $15\text{ V}$			0.8	V
Output Logic High (SDO)	$V_{OH}$	$R_{\text{Pull-up}} = 2.2\text{ k}\Omega$ to 5 V	4.9			V
Output Logic Low (SDO)	$V_{OL}$	$I_{OL} = 1.6\text{ mA}$ , $V_{\text{LOGIC}} = 5\text{ V}$ , $V_{DD} = 15\text{ V}$			0.4	V
Input Current	$I_{IL}$	$V_{IN} = 0\text{ V}$ or $5\text{ V}$			±1	μA
Input Capacitance <sup>6</sup>	$C_{IL}$			5		pF
<b>POWER SUPPLIES</b>						
Power Supply Range	$V_{DD}/V_{SS}$	Dual-supply range	±4.5		±16.5	V
Power Supply Range	$V_{DD}$	Single-supply range, $V_{SS} = 0$	4.5		33	V
Positive Supply Current	$I_{DD}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			2	mA
		$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 5\text{ V}$		12	25	μA
Negative Supply Current	$I_{SS}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			-0.1	mA
		$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 5\text{ V}$			-0.1	mA
Power Dissipation <sup>8</sup>	$P_{DISS}$	$V_{IH} = +5\text{ V}$ or $V_{IL} = 0\text{ V}$ , $V_{DD}/V_{SS} = \pm 15\text{ V}$			31.5	mW
Power Supply Rejection Ratio	PSRR		-0.25	±0.1	+0.25	%/%
<b>DYNAMIC CHARACTERISTICS<sup>6,7,8</sup></b>						
Bandwidth -3 dB	BW	$R_{AB} = 50\text{ k}\Omega$ , code = 0x80		90		kHz
		$R_{AB} = 100\text{ k}\Omega$ , code = 0x80		50		kHz
Total Harmonic Distortion	THD <sub>w</sub>	$V_A = 1\text{ V rms}$ , $V_B = 0\text{ V}$ , f = 1 kHz		0.002		%
$V_W$ Settling Time	$t_S$	$V_A = 10\text{ V}$ , $V_B = 0\text{ V}$ , ±1 LSB error band		4		μs
Resistor Noise Voltage	$e_{N\_WB}$	$R_{WB} = 25\text{ k}\Omega$ , f = 1 kHz		2		$nV\sqrt{\text{Hz}}$

<sup>1</sup> Typical represent average reading at +25°C,  $V_{DD} = +15\text{ V}$ , and  $V_{SS} = -15\text{ V}$ .

<sup>2</sup> Resistor position nonlinearity error R-INL is the deviation from an ideal value measured between the maximum resistance and the minimum resistance wiper positions. R-DNL measures the relative step change from an ideal value measured between successive tap positions. Parts are guaranteed monotonic.

<sup>3</sup> All parts have a 35 ppm/°C temperature coefficient.

<sup>4</sup> INL and DNL are measured at VW with the RDAC configured as a potentiometer divider similar to a voltage output digital-to-analog converter.  $V_A = V_{DD}$  and  $V_B = 0\text{ V}$ . DNL specification limits of ±1 LSB maximum are guaranteed monotonic operating conditions.

<sup>5</sup> Resistor Terminals A, B, and W have no limitations on polarity with respect to each other.

<sup>6</sup> Guaranteed by design and not subject to production test.

<sup>7</sup> Bandwidth, noise, and settling times are dependent on the terminal resistance value chosen. The lowest R value results in the fastest settling time and highest bandwidth. The highest R value results in the minimum overall power consumption.

<sup>8</sup> All dynamic characteristics use  $V_{DD} = +15\text{ V}$  and  $V_{SS} = -15\text{ V}$ .

**Table 3.**

INTERFACE TIMING CHARACTERISTICS <sup>1</sup>				
Clock Frequency	$f_{CLK}$		4	MHz
Input Clock Pulse Width	$t_{CH}, t_{CL}$	Clock level high or low	120	ns
Data Setup Time	$t_{DS}$		30	ns
Data Hold Time	$t_{DH}$		20	ns
CLK to SDO Propagation Delay <sup>2</sup>	$t_{PD}$	$R_{Pull-up} = 2.2\text{ k}\Omega, C_L < 20\text{ pF}$	10	100 ns
$\overline{CS}$ Setup Time	$t_{CSS}$		120	ns
$\overline{CS}$ High Pulse Width	$t_{CSW}$		150	ns
CLK Fall to $\overline{CS}$ Fall Hold Time	$t_{CSH0}$		10	ns
CLK Rise to $\overline{CS}$ Rise Hold Time	$t_{CSH}$		120	ns
$\overline{CS}$ Rise to Clock Rise Setup	$t_{CS1}$		120	ns

<sup>1</sup> See Figure 3 for the location of the measured values. All input control voltages are specified with  $t_R = t_F = 1\text{ ns}$  (10% to 90% of  $V_{DD}$ ) and timed from a voltage level of 1.6 V. Switching characteristics are measured using  $V_{DD} = +15\text{ V}$  and  $V_{SS} = -15\text{ V}$ .

<sup>2</sup> Propagation delay depends on value of  $V_{DD}$ ,  $R_{Pull-up}$ , and  $C_L$ .

### 3-WIRE DIGITAL INTERFACE

Table 4. AD5290 Serial Data-Word Format

B7	B6	B5	B4	B3	B2	B1	B0
D7	D6	D5	D4	D3	D2	D1	D0
MSB							LSB
$2^7$							$2^0$

NOTE: Data is loaded MSB first.

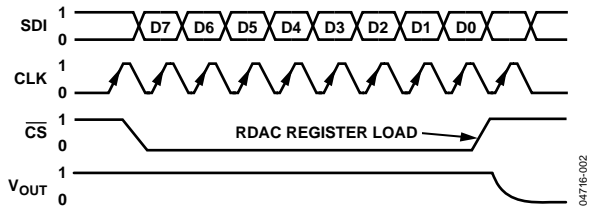


Figure 2. AD5290 3-Wire Digital Interface Timing Diagram  
 ( $V_A = V_{DD}$ ,  $V_B = 0V$ ,  $V_W = V_{OUT}$ )

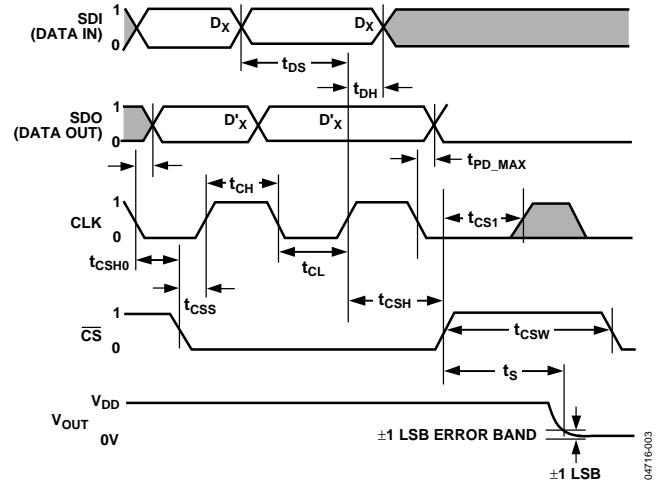


Figure 3. Detail Timing Diagram

## ABSOLUTE MAXIMUM RATINGS

$T_A = +25^\circ\text{C}$ , unless otherwise noted.

**Table 5.**

Parameter	Rating
$V_{DD}$ to GND	-0.3 V, +35 V
$V_{SS}$ to GND	+0.3 V, -16.5 V
$V_{DD}$ to $V_{SS}$	-0.3 V, +35 V
$V_A, V_B, V_W$ to GND	$V_{SS}, V_{DD}$
Maximum Current	
$I_{WB}, I_{WA}$ Pulsed	$\pm 20$ mA
$I_{WB}$ Continuous ( $R_{WB} \leq 6\text{k}\Omega$ , A Open, $V_{DD}/V_{SS} = 30\text{V}/0\text{V}$ ) <sup>1</sup>	$\pm 5$ mA
$I_{WA}$ Continuous ( $R_{WA} \leq 6\text{k}\Omega$ , B Open, $V_{DD}/V_{SS} = 30\text{V}/0\text{V}$ ) <sup>1</sup>	$\pm 5$ mA
Digital Input and Output Voltages to GND	0 V, +7 V
Operating Temperature Range	$-40^\circ\text{C}$ to $+125^\circ\text{C}$
Maximum Junction Temperature ( $T_J$ MAX) <sup>2</sup>	$+150^\circ\text{C}$
Storage Temperature	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10 to 30 sec)	$245^\circ\text{C}$
Thermal Resistance <sup>2</sup> $\theta_{JA}$ : MSOP-10	$230^\circ\text{C}/\text{W}$

<sup>1</sup> Maximum terminal current is bounded by the maximum current handling of the switches, maximum power dissipation of the package, and maximum applied voltage across any two of the A, B, and W terminals at a given resistance.

<sup>2</sup> Package power dissipation =  $(T_{JMAX} - T_A)/\theta_{JA}$ .

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.





## PIN CONFIGURATION AND DESCRIPTIONS

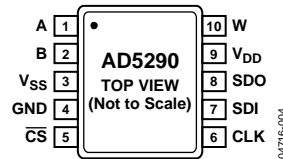


Figure 4. AD5290 Pin Configuration

Table 6. AD5290 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	A	A Terminal. $V_{SS} \leq V_A \leq V_{DD}$ .
2	B	B Terminal. $V_{SS} \leq V_B \leq V_{DD}$ .
3	$V_{SS}$	Negative Supply. Connect to zero volts for single-supply applications.
4	GND	Digital Ground.
5	$\overline{CS}$	Chip Select Input, Active Low. When $\overline{CS}$ returns high, data is loaded into the wiper register.
6	CLK	Serial Clock Input. Positive edge triggered.
7	SDI	Serial Data Input Pin. Shifts in one bit at a time on positive clock CLK edges. MSB loaded first.
8	SDO	Serial Data Output Pin. Internal N-Ch FET with open-drain output that requires external pull-up resistor. It shifts out the previous 8 SDI bits that allow daisy-chain operation of multiple packages.
9	$V_{DD}$	Positive Power Supply.
10	W	W Terminal. $V_{SS} \leq V_W \leq V_{DD}$ .

# TYPICAL PERFORMANCE CHARACTERISTICS

Figure 5. Resistance Step Position Nonlinearity Error vs. Code

Figure 6. Relative Resistance Step Change from Ideal vs. Code

Figure 7. Potentiometer Divider Nonlinearity Error vs. Code

Figure 8. Potentiometer Divider Differential Nonlinearity Error vs. Code

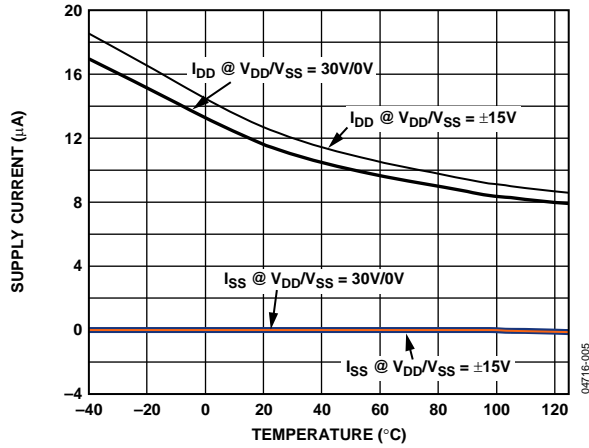


Figure 9. Supply Current (I<sub>DD</sub>, I<sub>SS</sub>) vs. Temperature

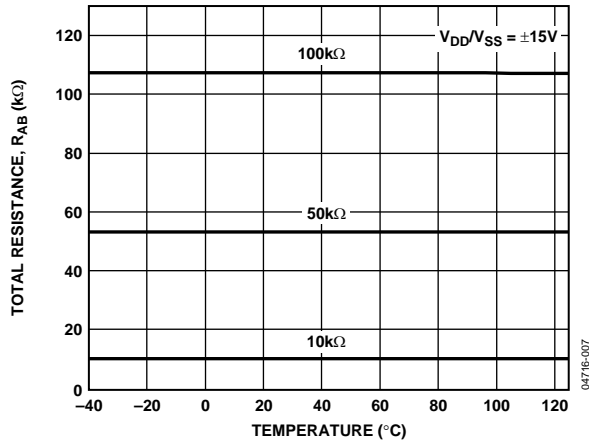


Figure 10. Total Resistance vs. Temperature

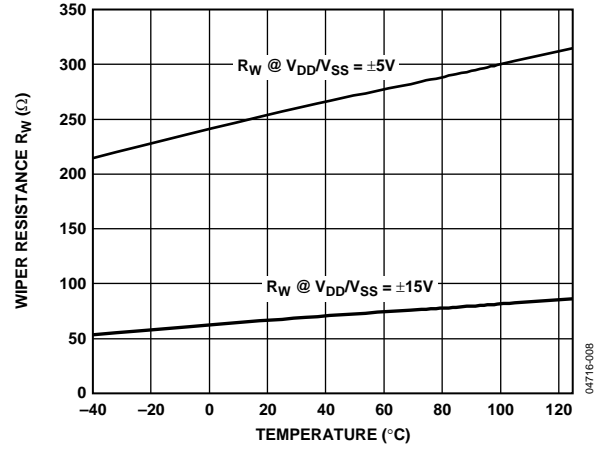


Figure 11. Wiper Contact Resistance vs. Temperature

Figure 12. (ΔR<sub>WB</sub>/R<sub>WB</sub>)/ΔT Rheostat Mode Tempco

Figure 13. (ΔV<sub>WB</sub>/V<sub>WB</sub>)/ΔT Potentiometer Mode Tempco

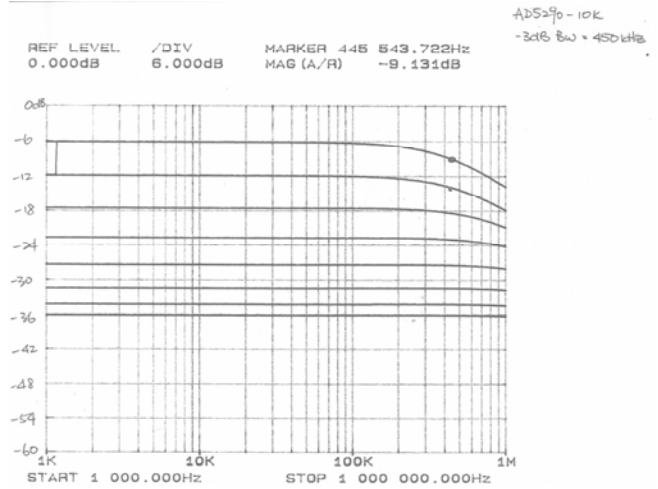


Figure 14. 10 kΩ Gain vs. Frequency vs. Code

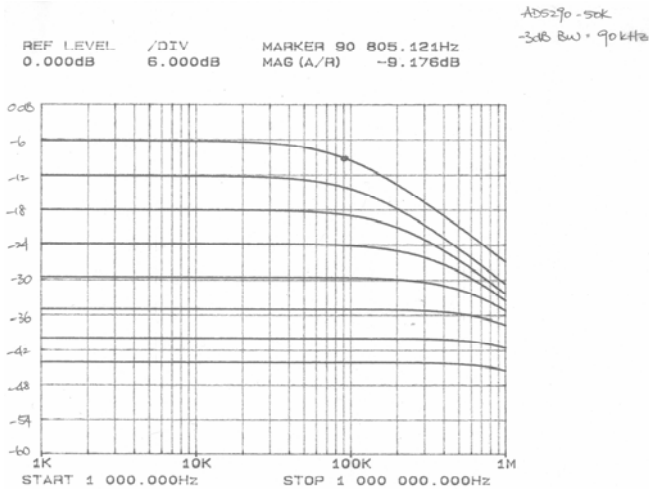


Figure 15. 50 kΩ Gain vs. Frequency vs. Code

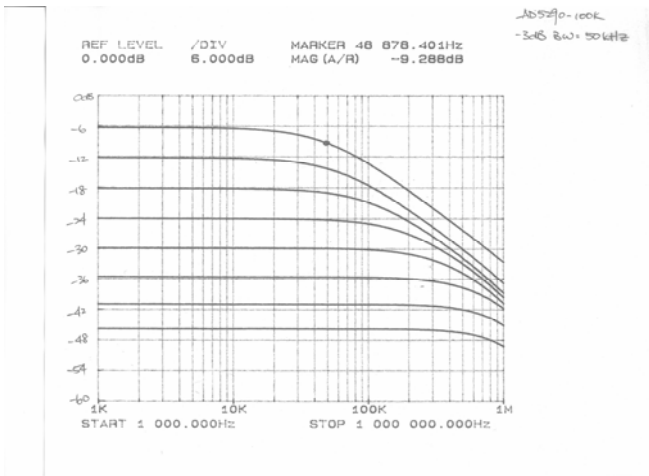


Figure 16. 100 kΩ Gain vs. Frequency vs. Code

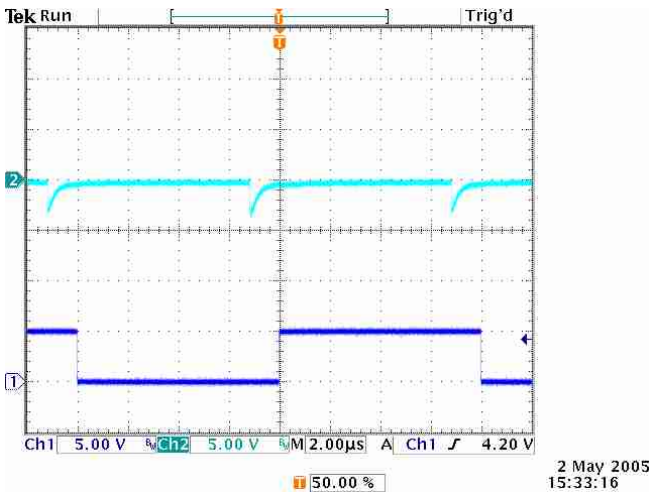


Figure 17. Midscale Transition Glitch

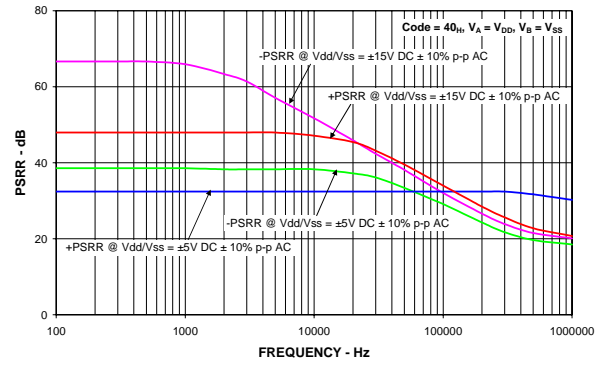


Figure 18. Power Supply Rejection vs. Frequency

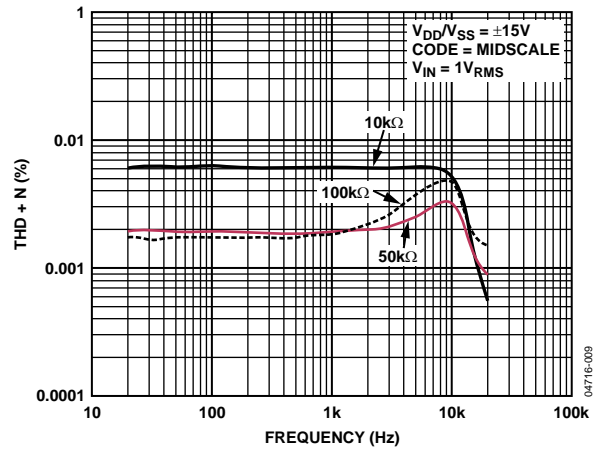


Figure 19. Total Harmonic Distortion Plus Noise vs. Frequency

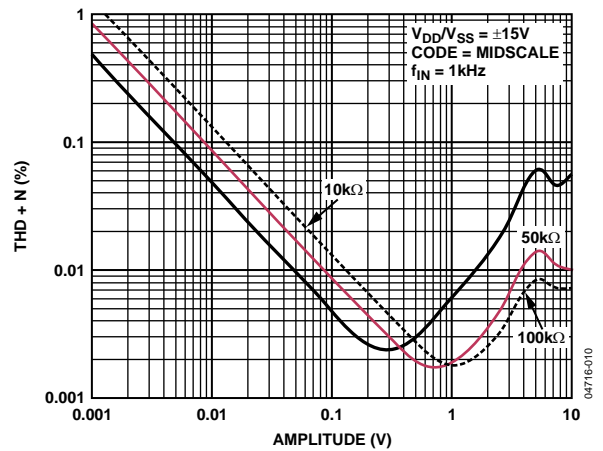


Figure 20. Total Harmonic Distortion Plus Noise vs. Amplitude

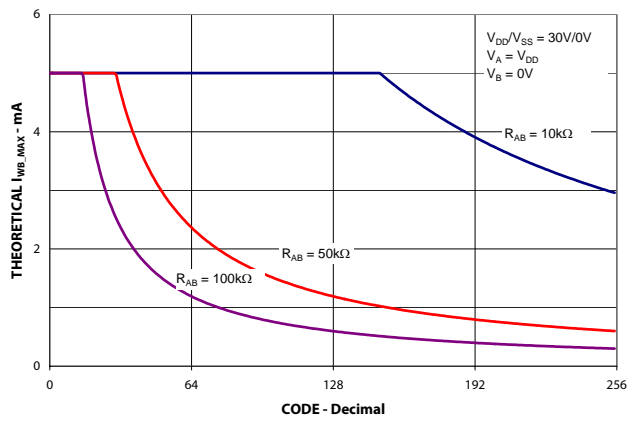


Figure 21. Theoretical Maximum Current vs. Code

## THEORY OF OPERATION

### PROGRAMMING THE VARIABLE RESISTOR

#### Rheostat Operation

When only two terminals are used, for example,  $R_{WA}$  or  $R_{WB}$  as shown in Figure 23, the part operates in rheostat mode. The nominal resistance between terminals A and B,  $R_{AB}$  is available in 10 k $\Omega$ , 50 k $\Omega$ , and 100 k $\Omega$  and has 256 tap points accessed by the wiper terminal. The 8-bit data in the RDAC latch is decoded to select one of the 256 possible settings, as shown in Figure 23.

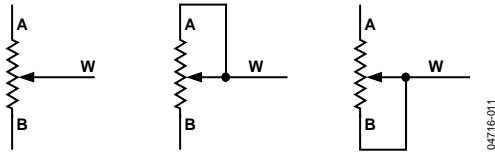


Figure 22. Rheostat Mode Configuration

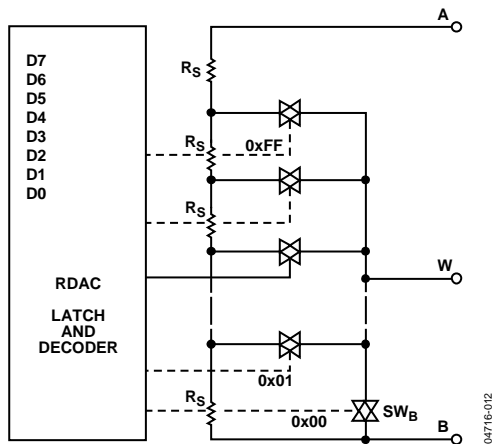


Figure 23. AD5290 Equivalent RDAC Circuit

The general equation determining the digitally programmed output resistance between the W and B terminals is

$$R_{WB}(D) = \frac{D}{256} \times R_{AB} + R_W \quad (1)$$

where:

$D$  is the decimal equivalent of the binary code loaded in the 8-bit RDAC register from 0 to 256.

$R_{AB}$  is the end-to-end resistance.

$R_W$  is the wiper resistance contributed by the on resistance of the internal switch.

The AD5290 wiper switches are designed with the transmission gate CMOS topology with the gate voltage derived from the  $V_{DD}$ . The switch on-resistance,  $R_W$ , is not only the function of  $V_{DD}$ , but also of temperature; see Figure 11. Additionally, the on resistance for each switch is insensitive to the tap point potential and remains relatively flat as 120  $\Omega$  typical at  $V_{DD}$  of 15V and the temperature of 25°C.

Assuming that a 10 k $\Omega$  part is used, the wiper's first connection starts at the B terminal for programming code of 0x00 where  $SW_B$  is closed. The minimum resistance between terminals W and B is, therefore, generally 120  $\Omega$ . The second connection is the first tap point, which corresponds to 159  $\Omega$  ( $R_{WB} = 1/256 \times R_{AB} + R_W = 39 \Omega + 120 \Omega$ ) for programming code of 0x01, and so on. Each LSB data value increase moves the wiper up the resistor ladder until the last tap point is reached at 10,080  $\Omega$  ( $R_{AB} - 1\text{LSB} + R_W$ ).

Note that in the zero-scale condition, a finite wiper resistance of 120  $\Omega$  is present. Care should be taken to limit the current conducted between the W and B terminals in this state to a maximum pulse current of no more than 20 mA. Otherwise, degradation or possible destruction of the internal switch contact can occur.

Similar to the mechanical potentiometer, the resistance of the RDAC between the W and A terminals also produces a digitally controlled complementary resistance,  $R_{WA}$ . When these terminals are used, the B terminal can be opened. Setting the resistance value for  $R_{WA}$  starts at a maximum value of resistance and decreases as the data loaded in the latch increases in value. The general equation for this operation is

$$R_{WA}(D) = \frac{256 - D}{256} \times R_{AB} + R_W \quad (2)$$

Typical device-to-device matching is process-lot dependent and may vary by up to  $\pm 30\%$ . Because the resistance element is processed in thin-film technology, the change in  $R_{AB}$  with temperature has a very low 35 ppm/ $^{\circ}\text{C}$  temperature coefficient.

## PROGRAMMING THE POTENTIOMETER DIVIDER

### Voltage Output Operation

The digital potentiometer easily generates a voltage divider at wiper-to-B and wiper-to-A proportional to the input voltage at A to B. Unlike the polarity of  $V_{DD}$  to GND, which must be positive, voltage across A to B, W to A, and W to B can be at either polarity.

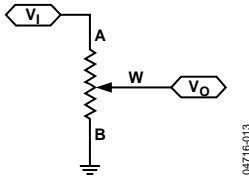


Figure 24. Potentiometer Mode Configuration

If ignoring the effect of the wiper resistance for approximation, connecting the A terminal to 30 V and the B terminal to ground produces an output voltage at the Wiper W to Terminal B ranging from 0 V to 1 LSB less than 30 V. Each LSB of voltage is equal to the voltage applied across terminals A and B, divided by the 256 positions of the potentiometer divider. The general equation defining the output voltage at  $V_W$  with respect to ground for any valid input voltage applied to terminals A and B is

$$V_W(D) = \frac{D}{256} V_A \quad (3)$$

A more accurate calculation, which includes the effect of wiper resistance,  $V_W$ , becomes

$$V_W(D) = \frac{R_{WB}(D)}{R_{AB}} V_A + \frac{R_{WA}(D)}{R_{AB}} V_B \quad (4)$$

Operation of the digital potentiometer in the divider mode results in a more accurate operation over temperature. Unlike the rheostat mode, the output voltage is dependent mainly on the ratio of the internal resistors  $R_{WA}$  and  $R_{WB}$  and not the absolute values. Therefore, the temperature drift reduces to 5 ppm/°C.

## 3-WIRE SERIAL BUS DIGITAL INTERFACE

The AD5290 contains a 3-wire digital interface ( $\overline{CS}$ , CLK, and SDI). The 8-bit serial word must be loaded MSB first. The format of the word is shown in Figure 2. The positive-edge sensitive CLK input requires clean transitions to avoid clocking incorrect data into the serial input register. Standard logic families work well. When  $\overline{CS}$  is high, the clock loads data into the serial register on each positive clock edge.

The data setup and data hold times in the specifications tables determine the valid timing requirements. The AD5290 uses an 8-bit serial input data register word that is transferred to the internal RDAC register when the  $\overline{CS}$  line returns to logic high. Extra MSB bits are ignored.

## DAISY CHAIN OPERATION

SDO shifts out the SDI content in the previous frame; thus it can be used for daisy chain multiple devices. The SDO pin contains an open drain N-Ch MOSFET and requires a pull-up resistor if SDO function is used. Users need to tie the SDO pin of one package to the SDI pin of the next package. Users may need to increase the clock period because the pull-up resistor and the capacitive loading at the SDO-SDI interface may induce time delay to the subsequent devices.

For example, in Figure 25, if two AD5290 are daisy-chained, a total of 16 bits of data are required for each operation. The first set of eight bits goes to U2, and the second set of eight bits goes to U1. The  $\overline{CS}$  should be kept low until all 16 bits are clocked into their respective serial registers. The  $\overline{CS}$  is then pulled high to complete the operation. When daisy chain multiple devices, users may need to increase the clock period because the pull-up resistor and the capacitive loading at the SDO-SDI interface may induce a time delay to subsequent devices.

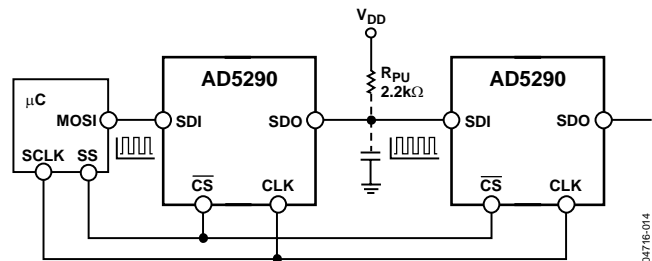


Figure 25. Daisy Chain Configuration

**ESD PROTECTION**

All digital inputs are protected with a series input resistor and a Zener ESD structure, as shown in Figure 26. These structures apply to digital input pins  $\overline{CS}$ , CLK, SDI, and SDO.

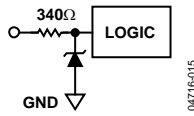


Figure 26. Equivalent ESD Protection Circuit

All analog terminals are also protected by Zener ESD protection diodes, as shown in Figure 27.

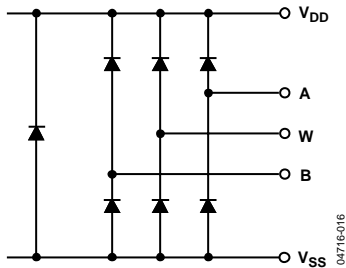


Figure 27. Equivalent ESD Protection Analog Pins

**TERMINAL VOLTAGE OPERATING RANGE**

The AD5290  $V_{DD}$  and  $V_{SS}$  power supplies define the boundary conditions for proper 3-terminal digital potentiometer operation. Applied signals present on Terminals A, B, and W that are more positive than  $V_{DD}$  or more negative than  $V_{SS}$  are clamped by the internal forward-biased diodes; refer to Figure 27.

**POWER-UP AND POWER-DOWN SEQUENCES**

Because of the ESD protection diodes that limit the voltage compliance at terminals A, B, and W (refer to Figure 27), it is important to power  $V_{DD}/V_{SS}$  before applying any voltage to

Terminals A, B, and W. Otherwise, the diodes are forward-biased such that  $V_{DD}/V_{SS}$  are powered unintentionally and affect the system. Similarly,  $V_{DD}/V_{SS}$  should be powered down last. The ideal power-up sequence is in the following order: GND,  $V_{DD}$ ,  $V_{SS}$ , digital inputs, and  $V_A/V_B/V_W$ . The order of powering  $V_A$ ,  $V_B$ ,  $V_W$ , and the digital inputs is not important, as long as they are powered after  $V_{DD}/V_{SS}$ .

**LAYOUT AND POWER SUPPLY BIASING**

It is good practice to use a compact, minimum lead-length layout design. The leads to the input should be as direct as possible, with a minimum conductor length. Ground paths should have low resistance and low inductance.

Similarly, it is also good practice to bypass the power supplies with quality capacitors. Low ESR (equivalent series resistance) 1  $\mu\text{F}$  to 10  $\mu\text{F}$  tantalum or electrolytic capacitors should be applied at the supplies to minimize any transient disturbance and filter low frequency ripple. Figure 28 illustrates the basic supply-bypassing configuration for the AD5290.

The ground pin of the AD5290 is a digital ground reference. To minimize the digital ground bounce, the AD5290 digital ground terminal should be joined remotely to the analog ground; refer to Figure 28.

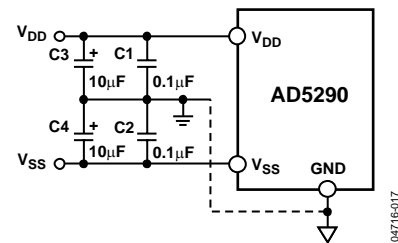


Figure 28. Power Supply Bypassing

## APPLICATIONS

### High Voltage DAC

AD5290 can be configured as a high voltage DAC, as high as 30 V. The circuit is shown in Figure 29. The output is

$$V_O(D) = \frac{D}{256} [1.2V \times (1 + \frac{R_2}{R_1})] \quad (5)$$

Where  $D$  is the decimal code from 0 to 255.

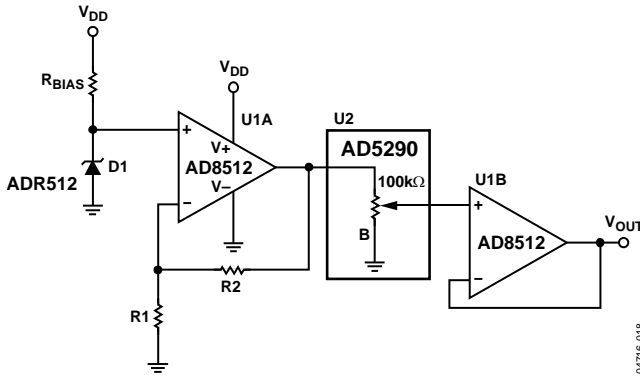


Figure 29. High Voltage DAC

### Programmable Power Supply

With a boost regulator, such as ADP1611, AD5290 can be used as the variable resistor at the regulator's FB pin to provide the programmable power supply; see Figure 31. The output is

$$V_O = 1.23V \times (1 + \frac{(D/256) \cdot R_{AB}}{R_2}) \quad (6)$$

Note that AD5290's  $V_{DD}$  is derived from the output. Initially,  $L1$  acts as a short, and  $V_{DD}$  is one diode voltage drop below +5 V. The output slowly establishes to the final value.

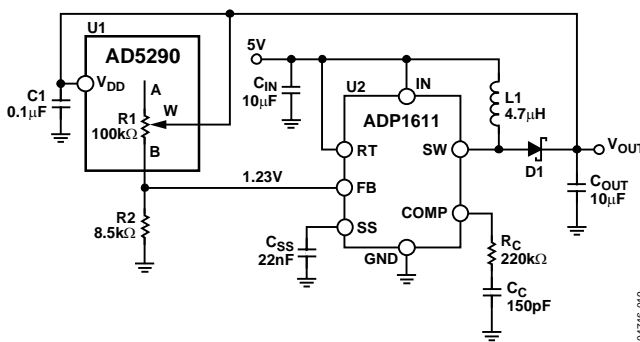


Figure 30. Programmable Power Supply

### Audio Volume Control

Because of its good THD performance and high voltage capability, AD5290 can be used as a digital volume control. If AD5290 is used directly as an audio attenuator or gain amplifier, a large step change in the volume level at any arbitrary time can lead to an abrupt discontinuity of the audio signal, causing an audible zipper noise. To prevent this, a zero-crossing window detector can be inserted to the  $CS$  line to delay the device update until the audio signal crosses the window. Since the input signal can operate on top of any dc levels rather than absolute zero volt level, zero-crossing in this case means the signal is ac coupled and the dc offset level is the signal zero reference point. The configuration to reduce zipper noise and the result of using this configuration are shown in (FIGURE 34 AUDIO VOLUME CONTROL WITH ZIPPER NOISE REDUCTION and FIGURE 35 Input (Trace 1) and Output (Trace 2) of the Circuit), respectively. The input is ac coupled by  $C1$  (Jim, please change  $C6$  to  $C1$ ) and attenuated down before feeding into the window comparator formed by  $U_2$ ,  $U_3$ , and  $U_{4B}$ .  $U_6$  is used to establish the signal zero reference. The upper limit of the comparator is set above its offset and, therefore, the output pulses high whenever the input falls between 2.502 V and 2.497 V (or 0.005 V window) in this example. This output is AND'd with the chip select signal such that the AD5290 updates whenever the signal crosses the window. To avoid constant update of the device, the chip select signal should be programmed as two pulses, rather than the one shown in FIGURE 2.

In FIGURE 35, the lower trace shows that the volume level changes from a quarter scale to full scale when a signal change occurs near the zero-crossing window.

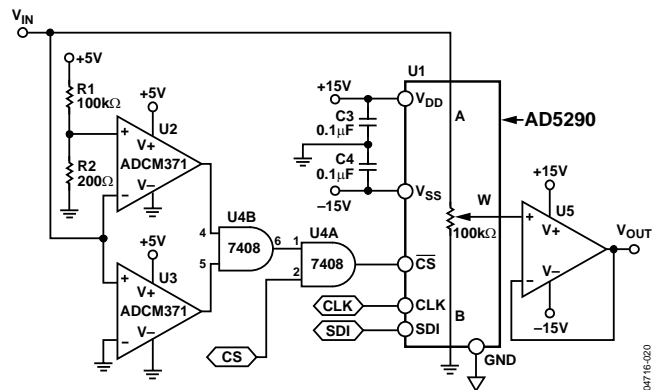


Figure 31. Audio Volume Control with Zipper Noise Reduction



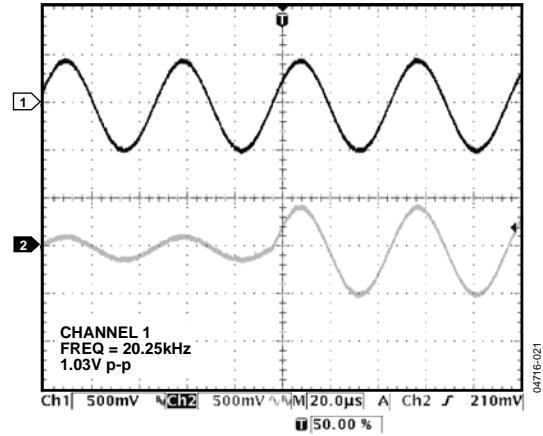
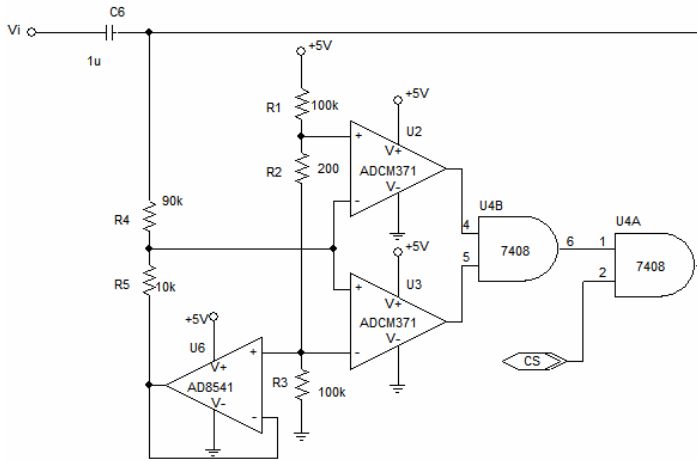


Figure 32. Input and output of the circuit in Figure 32. The lower trace shows that the volume level changes from a quarter scale to full scale with change occurs near zero crossing window.



**NOTES**

**NOTES**